## Phase transitions of LaTiO<sub>3</sub> under pressure

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The family of Ti-based RTiO<sub>3</sub> compounds, where R stands for a rare-earth ion, crystallize in the GdFeO<sub>3</sub>-type perovskite structure (SG *Pnma*, *Z*=4) at ambient conditions [1]. They all have a single electron in the  $t_{2g}$  orbitals of the Ti 3*d* shell (Ti<sup>3+</sup>) and are all Mott insulators [2,3]. Upon decreasing the ionic radius in the rare-earth series from La to Y, the structural distortions increase and, consequently, the one-electron bandwidth gets smaller [2,3]. LaTiO<sub>3</sub> exhibits the smallest structural distortions among the series and, concomitantly, has the smallest optical band gap ( $E_g \sim 0.1 \text{ eV}$  [1]). The latter implies that LaTiO<sub>3</sub> is on the verge of an insulator-to-metal transition. Indeed, previous high-pressure mid-infrared reflectivity investigations [4] detected the onset of an insulator-to-metal transition above 10 GPa.

The pressure-induced metallization motivated us to perform high-pressure x-ray diffraction (XRD) and Raman studies on LaTiO<sub>3</sub> in order to detect the response of the structure and the lattice dynamics. From our XRD study, we observe an *isostructural* transition taking place at ~10 GPa which coincides with the metallization of the compound. Upon further compression, the orthorhombic *Pnma* phase transforms into a tetragonal *I4/mcm* structure above 30 GPa. High-pressure Raman studies at ambient and low temperatures are consistent with the XRD results. We have observed an unusual enhancement of the Raman intensity upon entering the metallic state; a possible explanation of this peculiar behavior in terms of electronic correlations is offered.

## References

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